

FIG.1

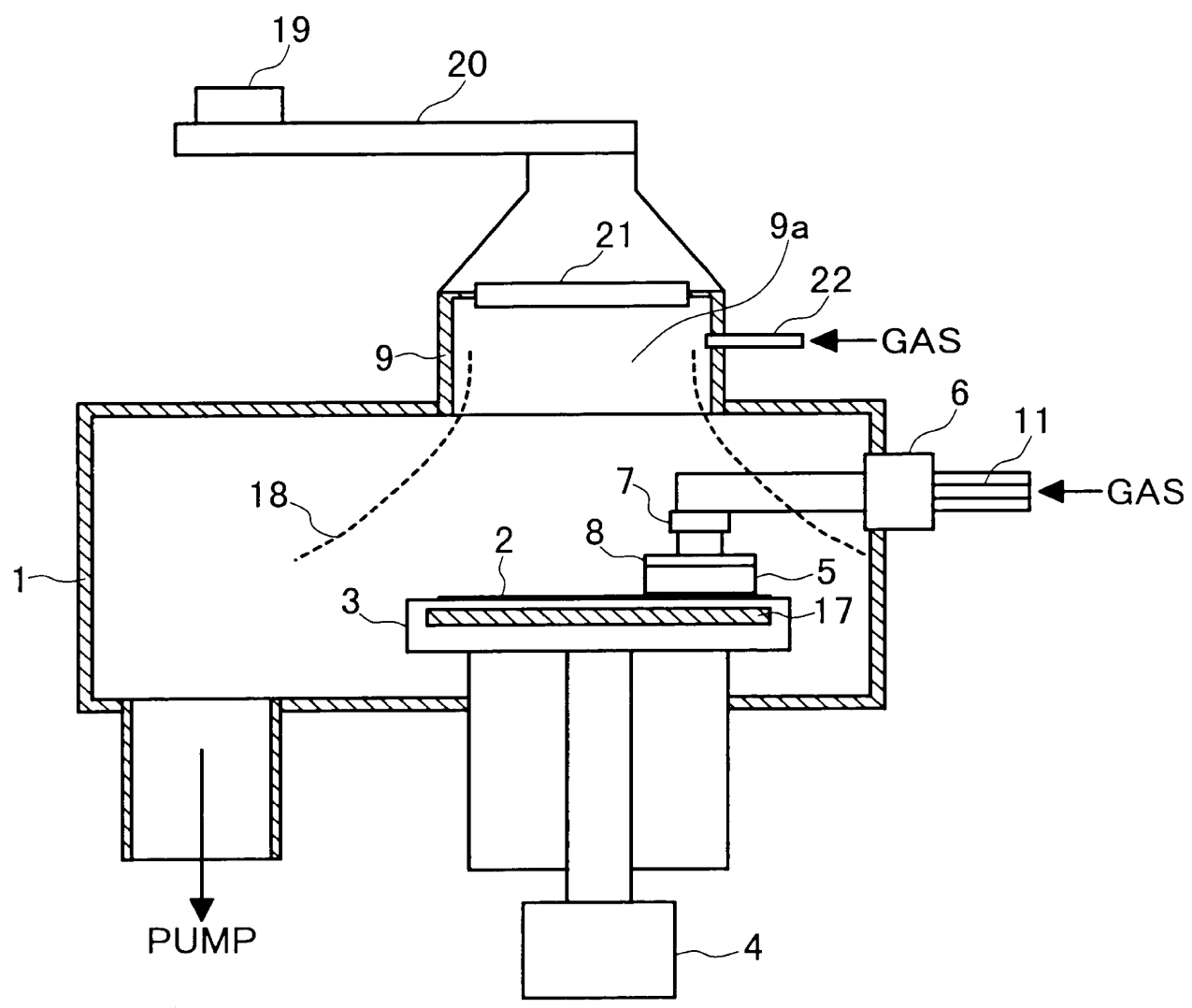


FIG.2

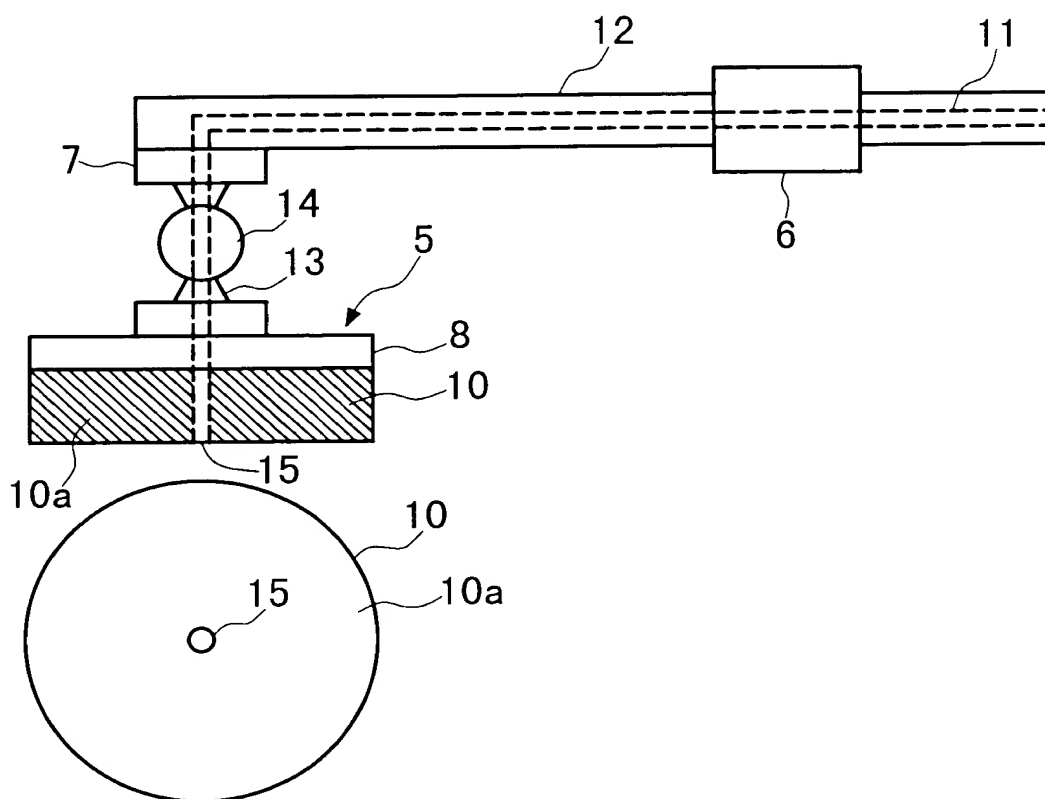


FIG.3

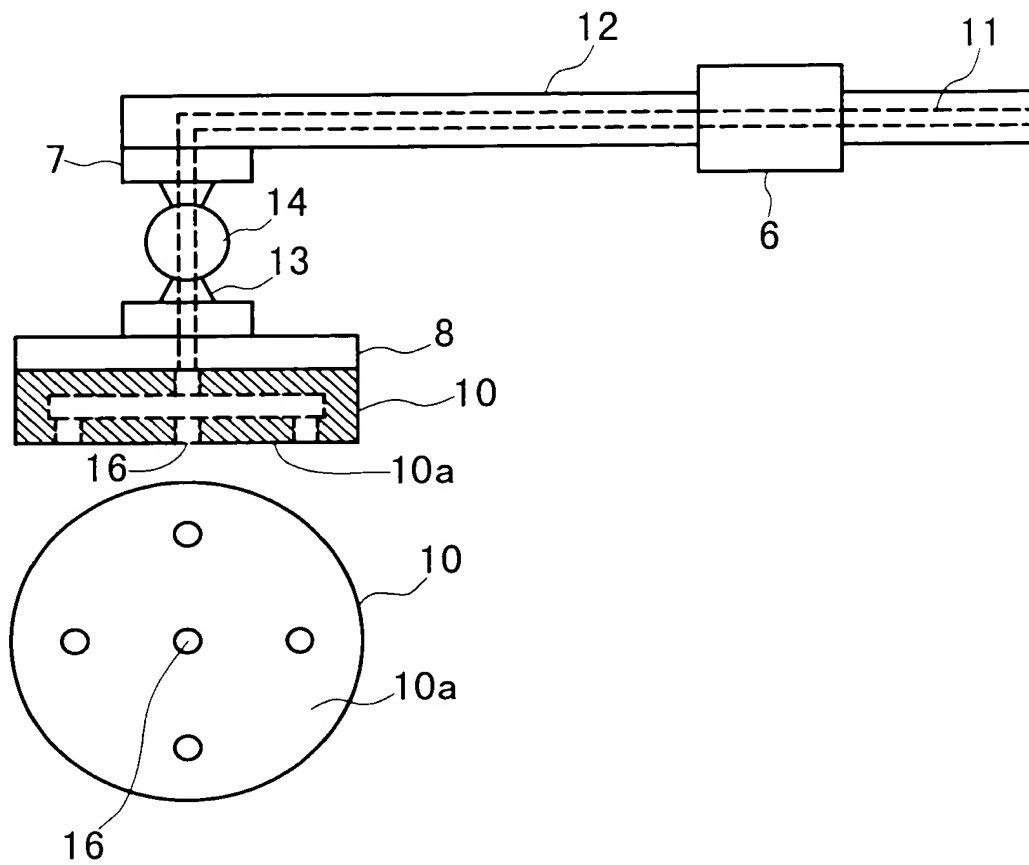


FIG.4

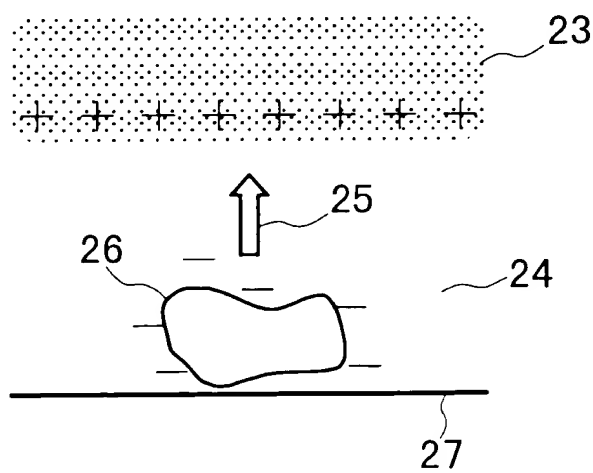


FIG.5

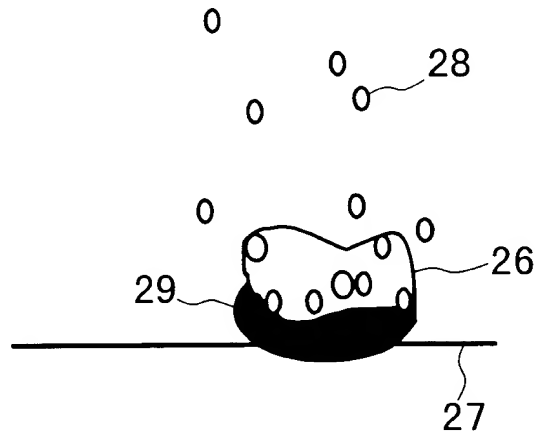


FIG.6

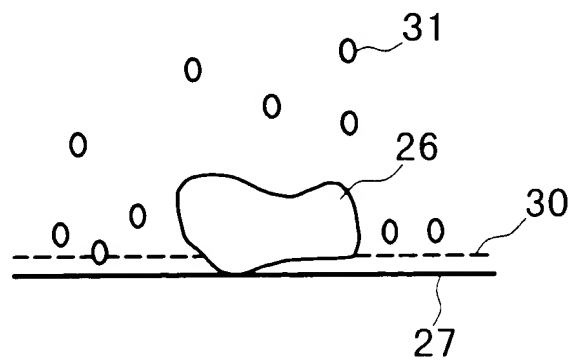


FIG. 7

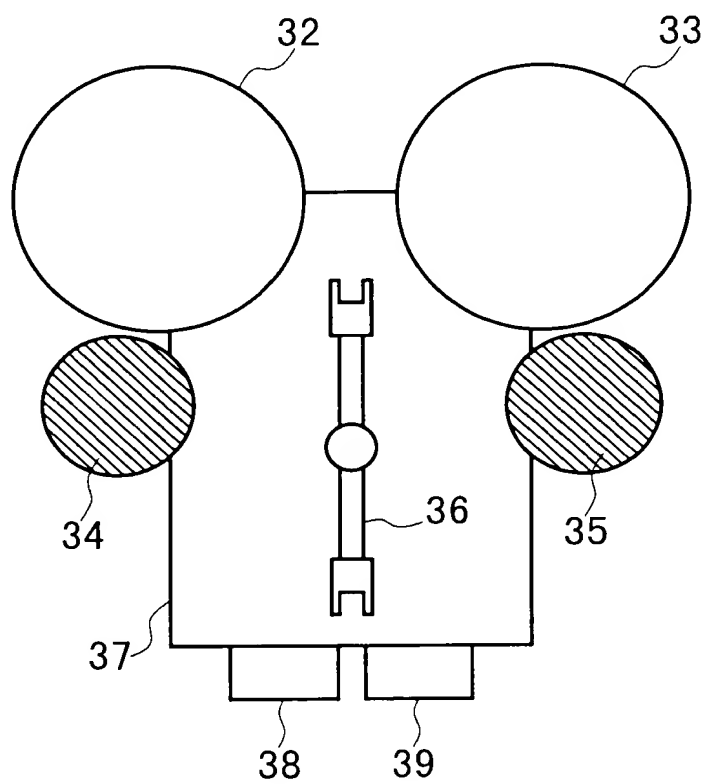


FIG.8

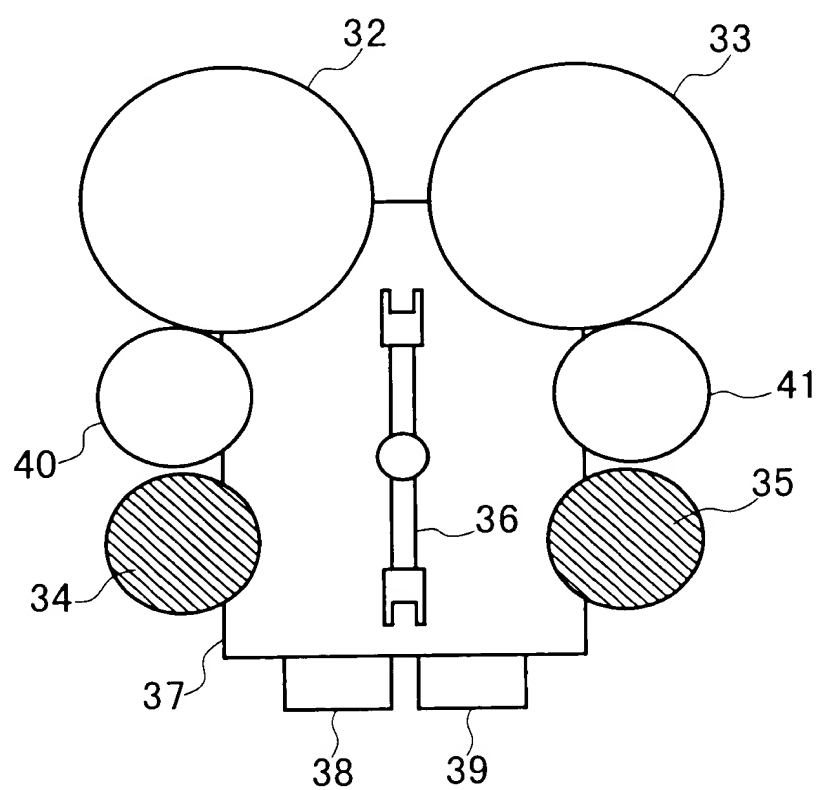


FIG.9

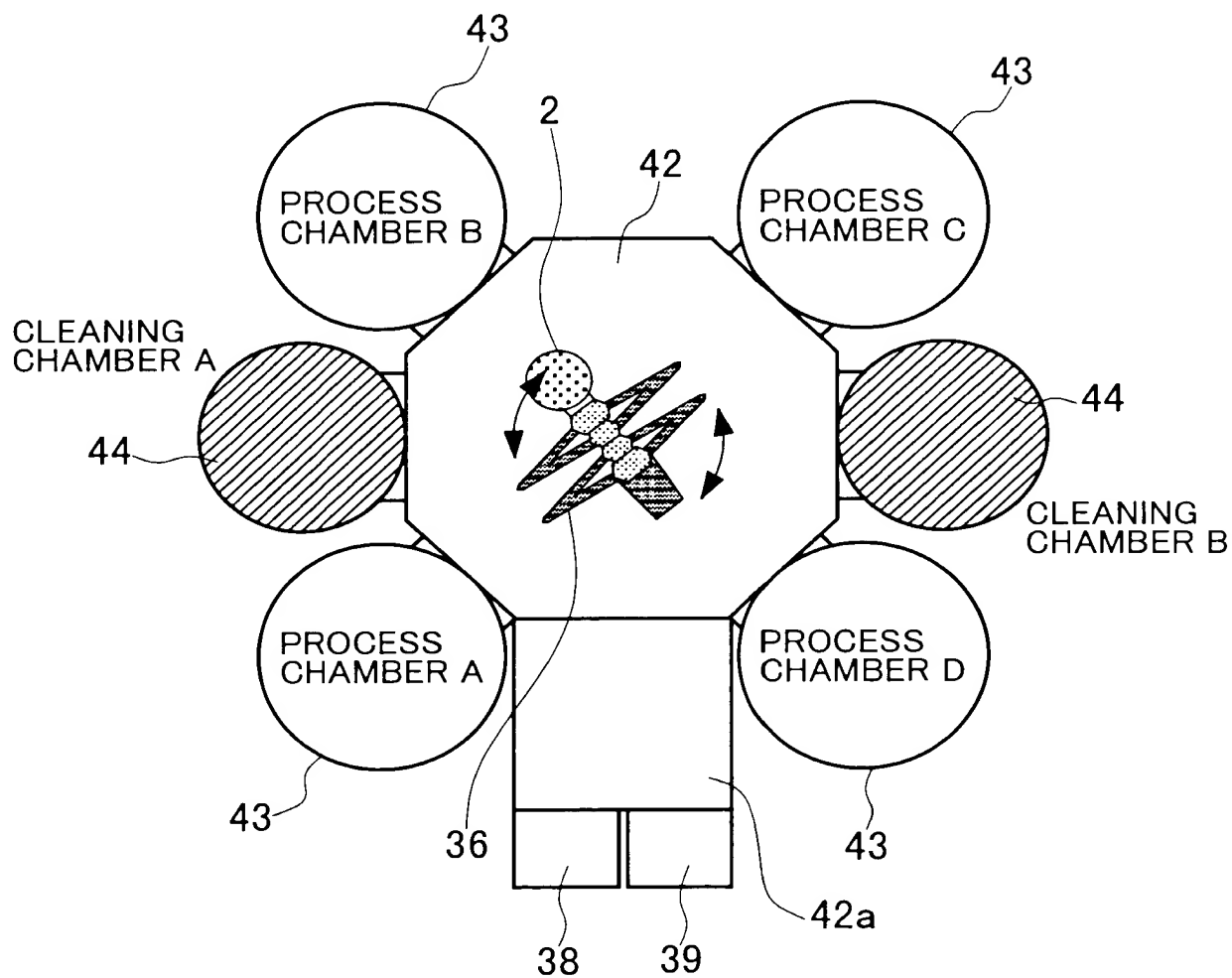


FIG.10A

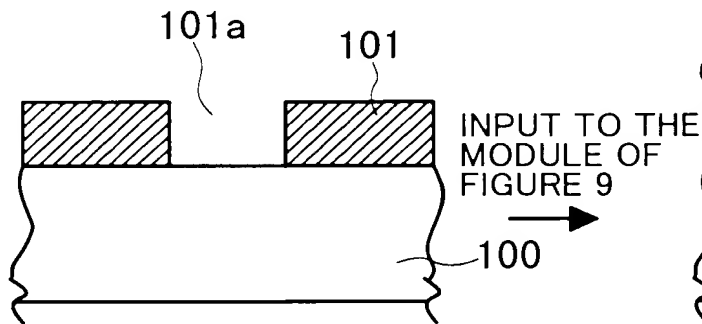


FIG.10B

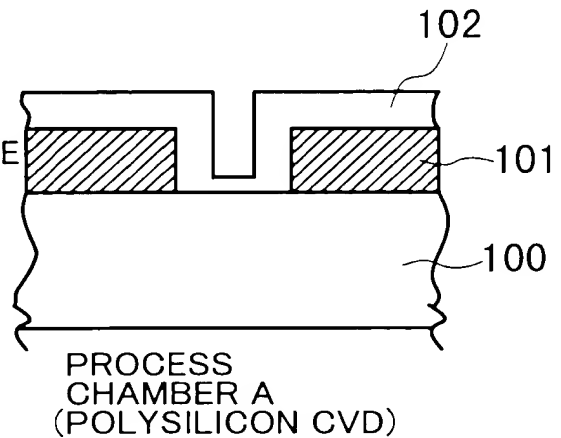


FIG.10C (CLEANING CHAMBER A)

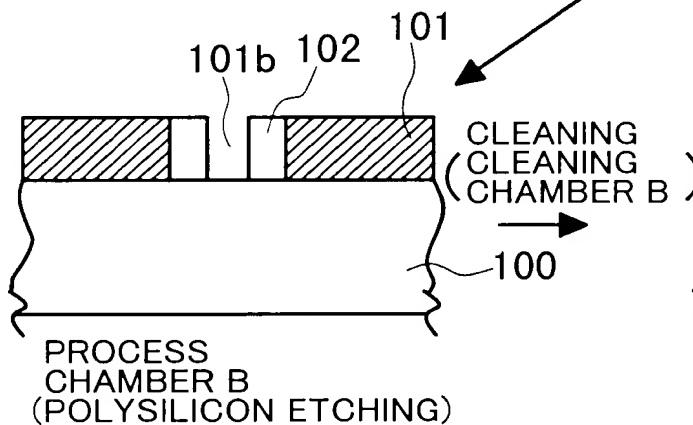


FIG.10D

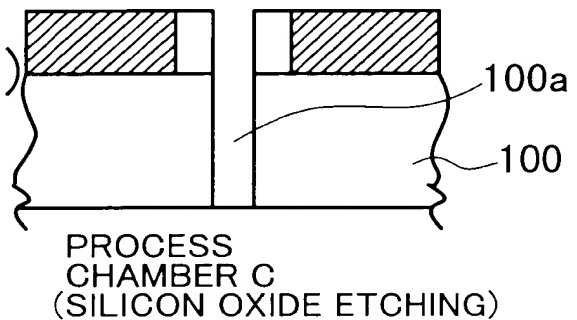


FIG.10E

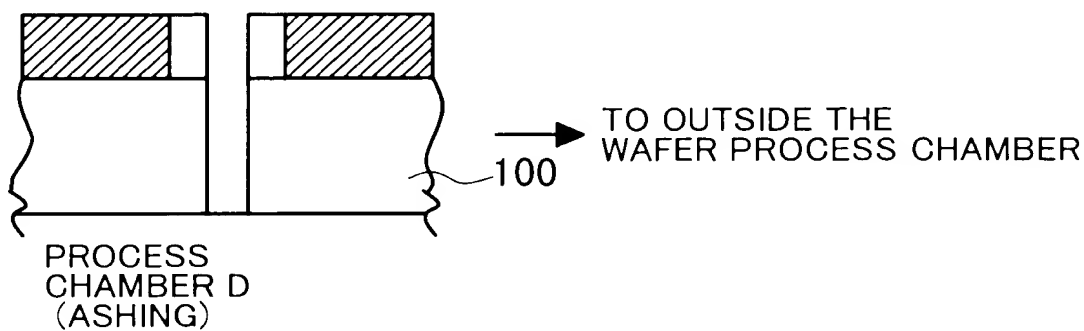


FIG.11A

FABRICATION
OF DEVICE ISOLATION
REGION AND DEPOSITION
OF POLYSILICON

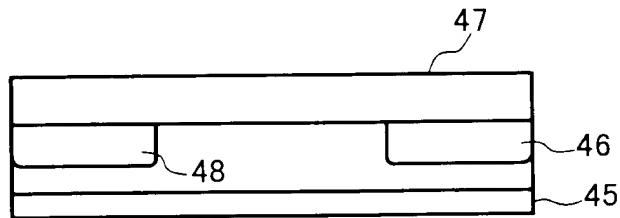


FIG.11B

FABRICATION
OF GATE ELECTRODE
(POLYSILICON ETCHING)

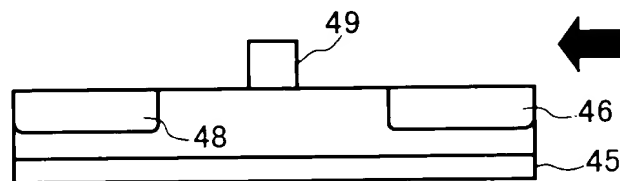


FIG.11C

FABRICATION
OF EXTENSION

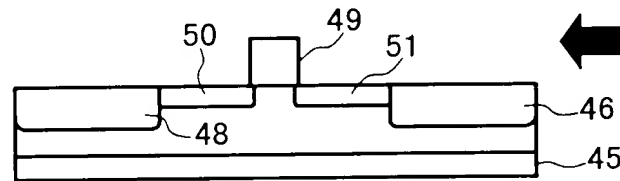


FIG.11D

DEPOSITION
OF NITRIDE FILM

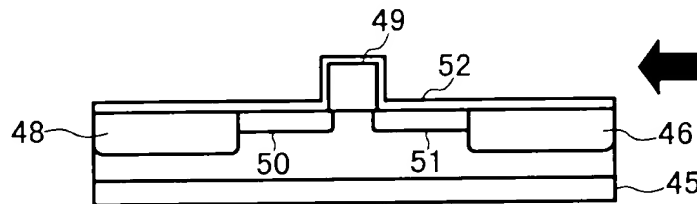


FIG.11E

FABRICATION
OF GATE SIDE
WALL FILM

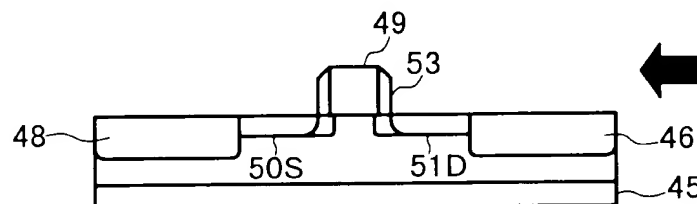


FIG.11F

FABRICATION
OF SILISIDE

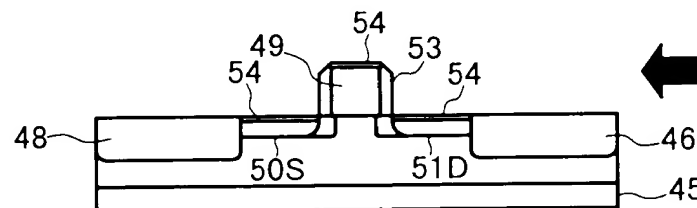


FIG.12A

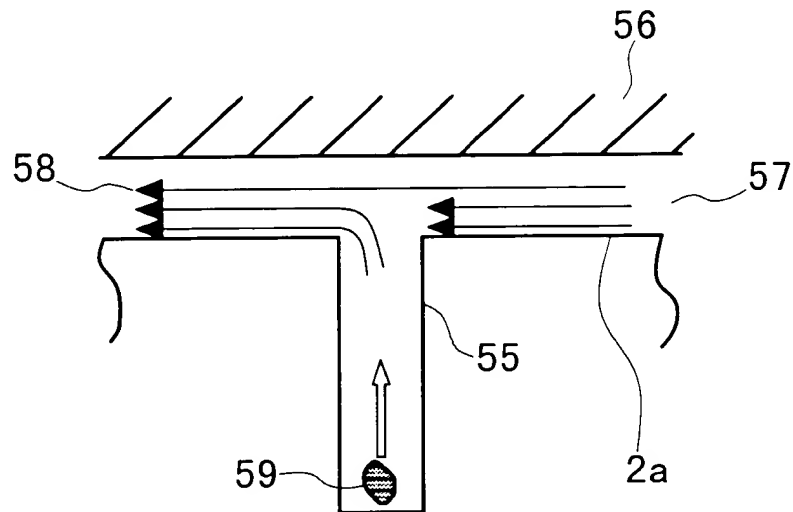


FIG.12B

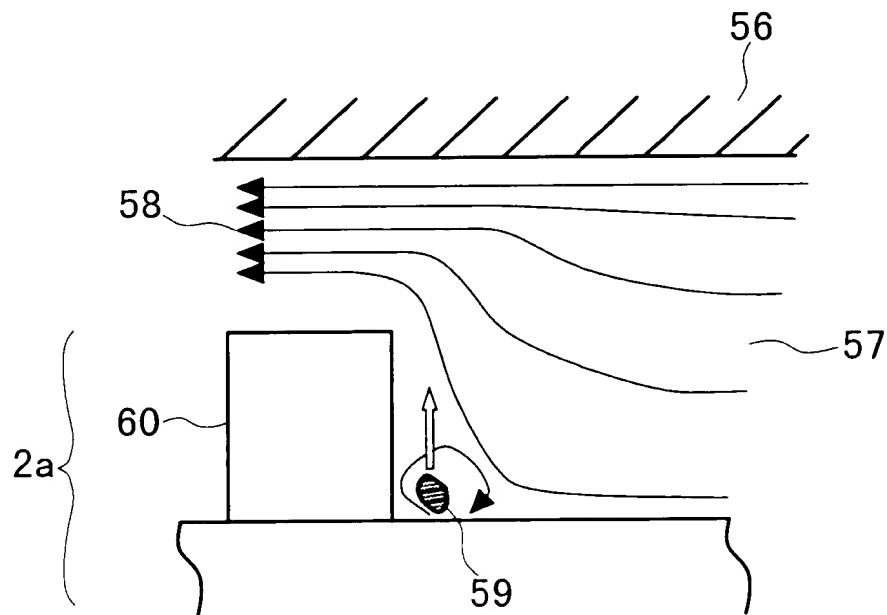


FIG.13

